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Correction: Spatial control of direct chemical vapor deposition of graphene on silicon dioxide by directional copper dewetting

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Correction for 'Spatial control of direct chemical vapor deposition of graphene on silicon dioxide by directional copper dewetting' by Wesley T. E. van den Beld *et al.*, *RSC Adv.*, 2016, 6, 89380–89386.

A reference related to the technique reported in this paper is missing from the original article. The graphene deposition process in the article is based on the dewetting of copper into grooves with simultaneous graphene deposition. A similar technique based on a two-step process – dewetting of copper with subsequent graphene deposition – had previously been published. The missing reference is listed herein as ref. 1 and should be cited in the original paper in the introduction. The relevant sentences from the introduction are given below with the corrected referencing and text; the reference number 1 refers to the new reference given herein, while the numbers 19–23 refer to the references given in the original manuscript:

Other research has shown that direct graphene synthesis is possible by dewetting of thin copper films on silica substrates using a CVD protocol.^{1,19} A common disadvantage of this route is that dewetting copper on a flat substrate results in a randomly distributed patchy graphene pattern or that copper etching is required to reveal the deposited graphene.^{1,19–23}

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

References

- 1 T. Kaplas and Y. Svirko, *Carbon*, 70, 273–278.

